



Micro Commercial Components
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2SD1710

NPN Silicon Power Transistors

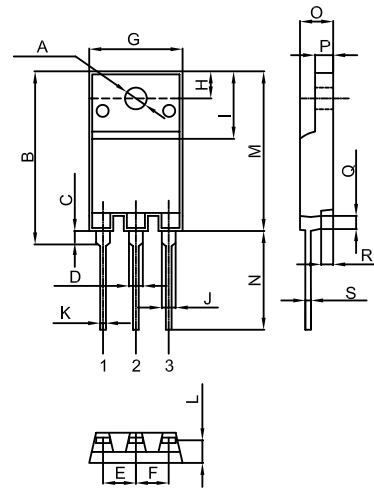
Features

- High voltage, high speed switching NPN transistors.
- With TO-3PML package
- Intended for use in horizontal deflection circuits of color television receivers.

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	800	V
V_{CBO}	Collector-Base Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current	5.0	A
P_C	Collector power dissipation	50	W
T_J	Junction Temperature	-55 to +150	$^{\circ}C$
T_{STG}	Storage Temperature	-55 to +150	$^{\circ}C$

TO-3PML



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=100mA$, $I_B=0$)	800	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=1500Vdc$, $I_E=0$)	---	1.0	mAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=6.0Vdc$, $I_C=0$)	---	10	mAdc

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=0.5Adc$, $V_{CE}=5.0Vdc$)	8.0	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=4.5Adc$, $I_B=2.0Adc$)	---	5.0	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=4.5Adc$, $I_B=2.0Adc$)	---	1.1	Vdc

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.13	.14	3.20	3.60	∅
B	.81	.84	20.70	21.30	
C	.15	.17	3.80	4.20	
D	.10	.12	2.50	3.10	
E	.21	.22	5.25	5.65	
F	.21	.22	5.25	5.65	
G	.62	.64	15.80	16.20	
H	.19	.21	4.70	5.30	
I	.30	.33	7.70	8.30	
J	.07	.09	1.70	2.30	
K	.03	.05	.70	1.30	
L	.13	.15	3.20	3.80	
M	.85	.88	21.70	22.30	
N	.78	.82	19.90	20.90	
O	.21	.23	5.30	5.90	
P	.11	.13	2.80	3.40	
Q	.07	.09	1.70	2.30	
R	.07	.09	1.70	2.30	
S	.02	.03	.40	.80	